

isc Silicon PNP Power Transistor

2SA1145

DESCRIPTION

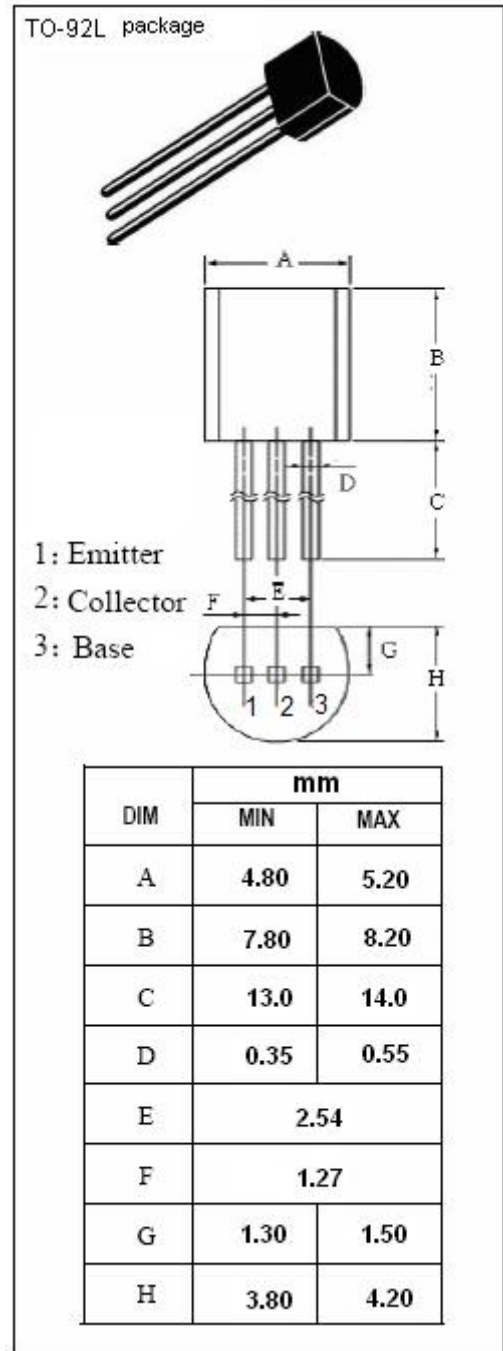
- Low collector output capacitance
- High frequency
- Complement to 2SC2705
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Audio frequency amplifier application

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	-150	V
V _{CEO}	Collector-Emitter Voltage	-150	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current-Continuous	-50	mA
P _C	Total Power Dissipation @ T _C =25°C	0.8	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



isc Silicon PNP Power Transistor**2SA1145****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -1mA; I _B = 0	-150			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -10mA; I _B = -1mA			-1	V
V _{BE(on)}	Base-Emitter Voltage	I _C = -10mA; V _{CE} = -5V			-0.8	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -150V; I _E = 0			-0.1	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-0.1	μ A
h _{FE}	DC Current Gain	I _C = -10mA; V _{CE} = -5V	80		240	
f _T	Current-Gain—Bandwidth Product	I _C = -10mA; V _{CE} = -10V		200		MHz
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V; f= 1MHz		2.5		pF

◆ **h_{FE} Classifications**

O	Y
80-160	120-240

isc Silicon PNP Power Transistor

2SA1381

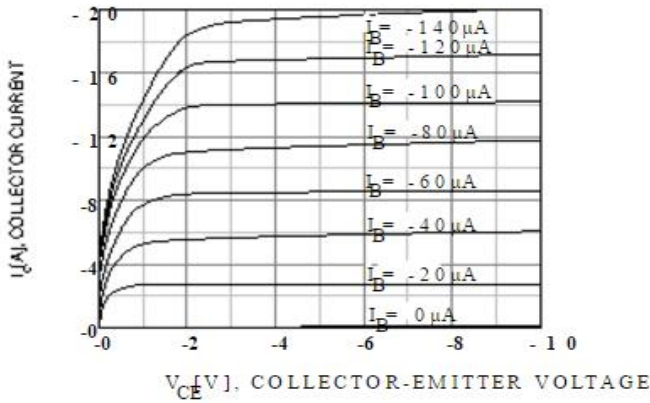


Figure 1. Static Characteristic

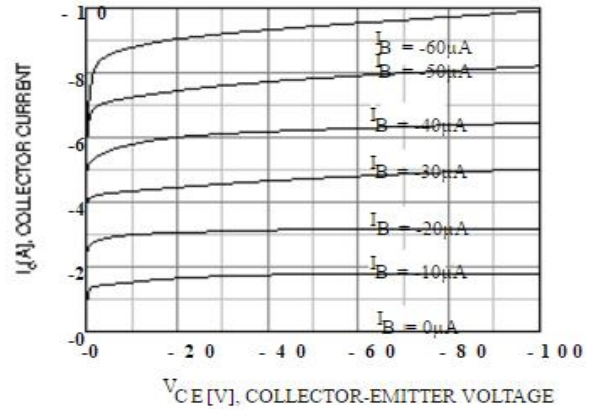


Figure 2. Static Characteristic

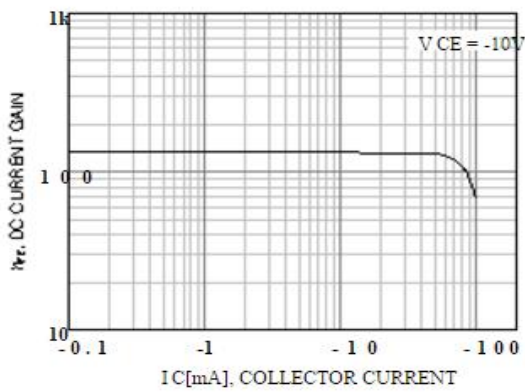


Figure 3. DC current Gain

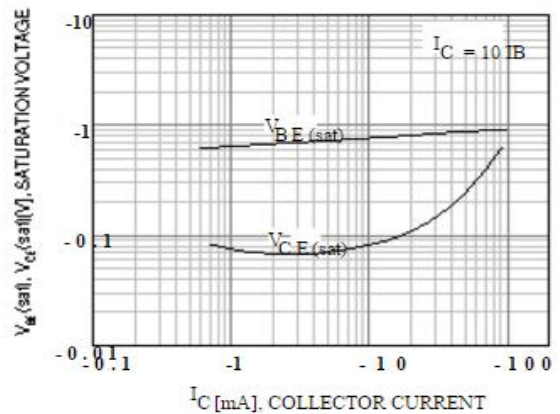


Figure 4. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

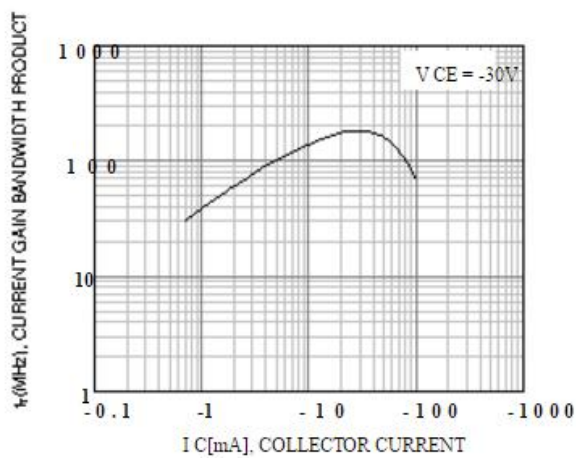


Figure 5. Current Gain Bandwidth Product

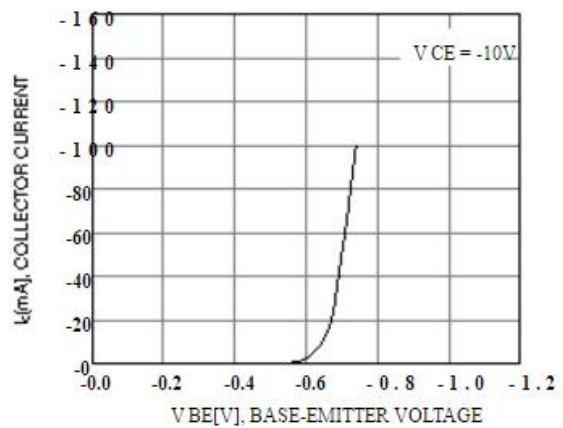


Figure 6. Base-Emitter On Voltage